

Zener Diode Chips for ESD Protection

1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge (ESD) protection application
- 1-2 This specification applies to N-Type silicon Zener diode chip Device NO:WT-Z106N-AU4

2. Structure:

- 2-1 Planar type: N/P Diode
- 2-2 Electrodes:
Top side:Gold Pad.(Cathode)
Back side:Gold Layer.(Anode)

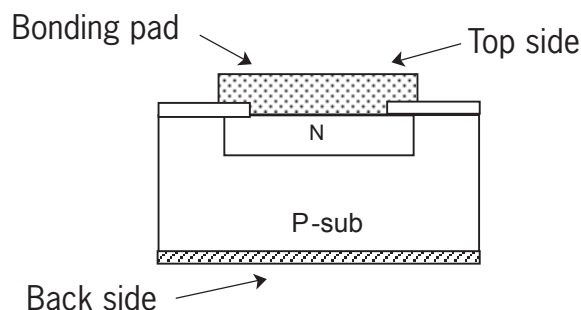
3. Size:

- 3-1 Chip size: 6.88 mils x 6.88 mils (175 μ m x 175 μ m).
- 3-2 Chip thickness: 3.3 $\pm$ 0.6 mils (85 μ m $\pm$ 15 μ m).
- 3-3 Active area: 4.1 mils x 4.1 mils (105 μ m x 105 μ m).
- 3-4 Bonding pad: 4.5 mils x 4.5mils (115 μ m x 115 μ m).
- 3-5 Pattern drawing: Refer to the attached drawing.

4. Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	V _z	I _z =5mA	5.7	-	6.7	V
Reverse Leakage Current	I _R	V _R =4V	-	-	100	nA
Forward Voltage	V _f	I _F =20mA	-	-	1.2	V
Electrostatic Discharge	ESD	HBM MIL-STD883	8	-	-	KV

5. Drawing:



www.DataSheet4U.com